TENTATIVE DATA 262,144 WORD ×4 BIT DYNAMIC RAM

DESCRIPTION

The TC514256AP/AJ/AZ is the new generation dynamic RAM organized 262,144 words by 4 bits. The TC514256AP/AJ/AZ utilizes TOSHIBA's CMOS Silicon gate process technology as well as advanced circuit techniques to provide wide operating margins, both internally and to the system user. Multiplexed address inputs permit the TC514256AP/AJ/AZ to be packaged in a standard 20 pin plastic DIP, 26/20 pin plastic SOJ and 20/19 pin plastic ZIP. The package size provides high system bit densities and is compatible with widely available automated testing and insertion equipment. System oriented features include single power supply of 5V±10% tolerance, direct interfacing capability with high performance logic families such as Schottky TTL.

FEATURES

- 262.144 word by 4 bit organization
- · Fast access time and cycle time

		TC514256AP/AJ/AZ - 70/ - 80/ - 10					
tasi	BAS Across Force	70ns	80ns	100ns			
taa	Column Asimess Access Toda	35ns	40ns	50ns			
tCAC	CAS Access Time	20ns	20ns	25ns			
tRC	Cycle Time	130ns	150ns	180ns			
tpc	Fast Page Mode Cycle Time	40ns	45ns	55ns			

 Single power supply of 5V±10% with a built-in VBB generator

PIN NAMES

A0~A8	Address Inputs	1/01~1/04	Data Input/Output
RAS	Row Address Strobe	V _{CC}	Power (+ 5V)
CAS	Column Address Strobe	Vss	Ground
WRITE	Read/Write Input	N.C.	No Connection
ŌĒ	Output Enable		

• Low Power

440mW MAX. Operating (TC514256AP/AJ/AZ-70) 385mW MAX. Operating (TC514256AP/AJ/AZ-80) 330mW MAX. Operating (TC514256AP/AJ/AZ-10) 5.5mW MAX. Standby

 Outputs unlatched at cycle end allows twodimensional chip selection

 Read-Modify-Write, CAS before RAS refresh, RAS-only refresh, Hidden refresh, and Fast Page Mode capability

· All inputs and outputs TTL compatible

512 refresh cycles/8ms

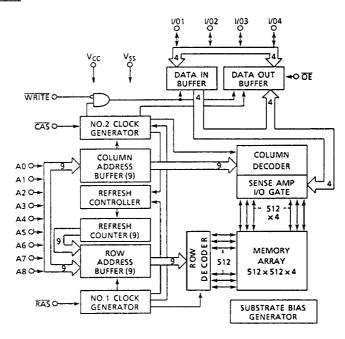
Package ŤC514256AP : DIP20-P-300B TC514256AJ : SOJ26-P-300

TC514256AJ : SOJ26-P-300 TC514256AZ : ZIP20-P-400

PIN CONNECTION (TOP VIEW)

Plastic	c DIP	Plasti	c SOI	Plastic	: ZIP
#01 L1 #00 C2 WRITE C3 RAS C4 N C. C5 A0 C6 A1 C7 A2 C8 A3 C9 Vcc C10	201V ₅₅ 191V ₆₄ 1811903 1710A5 1610E 151A8 141A7 131A6 121A5 111A4	1/01[1] 1/02[2 WRITEL 3 RAS 1 4 N.C. 15 A0 [9 A1 [10 A 2 [11] A 3 [12 Vcc [13	26 JVss 25 JV04 24 JV03 23 JCAS 22 JOE 18 JA8 17 JA7 16 JA6 15 JA5 14 JA4	OE 1. 3 1/03 3. 1 Vss 5. 3 1/02 7. 3 RAS 9. 3 AO 111 A2 133 Vcc 153 A5 172 A7 193	72 CAS 1/04 1/01 WRITE 112 A1 114 A3 116 A4 118 A6 20 A8

BLOCK DIAGRAM



MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT	NOTE
Input Voltage	V _{IN}	- 1~7	v	1
Output Voltage	Vout	- 1~7	v	1
Power Supply Voltage	Vcc	-1~7	V	1
Operating Temperature	TOPR	0~70	• c	1
Storage Temperature	TSTG	- 55~ 150	• c	1
Soldering Temperature · Time	TSOLDER	260 · 10	*C - sec	1
Power Dissipation	PD	600	mW	1
Short Circuit Output Current	lout	50	mA	1

RECOMMENDED DC OPERATING CONDITIONS (Ta = 0~70°c)

SYMBOL	CHARACTERISTIC	M≀N.	TYP.	MAX.	UNIT	NOTE
Vcc	Supply Voltage	4.5	5.0	5.5	٧	2
V _{IH}	Input High Voltage	2.4	-	6.5	>	2
V _{IL}	Input Low Voltage	- 1.0	-	0.8	٧	2

DC ELECTRICAL CHARACTERISTICS ($V_{CC} = 5V \pm 10\%$, $T_0 = 0 \sim 70$ °c)

SYMBOL	CHARACTERISTIC		MIN.	MAX.	UNIT	NOTE
	OPERATING CURRENT	TC514256AP/AJ/AZ-70	-	80		
lcc1	Average Power Supply Operating Current	TC514256AP/AJ/AZ-80	-	70	mA	3, 4, 5
	(RAS, CAS, Address Cycling: t _{RC} = t _{RC} MIN.)	TC514256AP/AJ/AZ-10	-	60		
I _{CC2}	STANDBY CURRENT Power Supply Standby Current (RAS = CAS = V _{IH})		_	2	mA	
	RAS ONLY REFRESH CURRENT	TC514256AP/AJ/AZ-70	_	80		
I _{CC3}	Average Power Supply Current, RAS Only Mode	TC514256AP/AJ/AZ-80	<u>-</u>	70	mA.	3, 5
	(RAS Cycling, CAS = VIH: tRC = tRC MIN.)	TC514256AP/AJ/AZ-10	-	60		
	FAST PAGE MODE CURRENT	TC514256AP/AJ/AZ-70		60		
	Average Power Supply Current, Fast Page Mode	TC514256AP/AJ/AZ-80	-	50	mA	3, 4, 5
I _{CC4}	$(\overline{RAS} = V_{IL}, \overline{CAS}, Address Cycling: t_{PC} = t_{PC} MIN.)$	TC514256AP/AJ/AZ-10	-	40		
Iccs	STANDBY CURRENT Power Supply Standby Current (RAS = CAS = V _{CC} – 0.2V)		-	1	mA	
	CAS BEFORE RAS REFRESH CURRENT	TC514256AP/AJ/AZ-70	-	80		
ICCE	Average Power Supply Current, CAS Before RAS	TC514256AP/AJ/AZ-80	-	70	mA	3
	Mode (RAS, CAS Cycling: t _{RC} = t _{RC} MIN.)	TC514256AP/AJ/AZ-10	-	60		
^ί ι (L)	INPUT LEAKAGE CURRENT Input Leakage Current, any input $(0V \le V_{IN} \le 6.5V$, All Other Pins Not Under Test = 0V)		- 10	10	μА	
lo (L)	OUTPUT LEAKAGE CURRENT (D _{OUT} is disabled, 0V≤V _{OUT} ≤5.5V)		- 10	10	μА	
V _{ОН}	OUTPUT LEVEL Output "H" Level Voltage (I _{OUT} = -5mA)		2.4	-	٧	
Vol	OUTPUT LEVEL Output "L" Level Voltage (I _{OUT} = 4.2mA)		-	0.4	٧	

ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS $(V_{CC} = 5V \pm 10\%, Ta = 0 \sim 70^{\circ}c)$ (Notes 6, 7, 8)

SYMBOL	CHARACTERISTIC		4256AP/ /AZ-70		4256AP/ /AZ-80		4256AP/ /AZ-10	UNIT	NOTE
311111000		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
t _{RC}	Random Read or Write Cycle Time	130	-	150	-	180	1	ns	
t _{RMW}	Read-Modify-Write Cycle Time	185	-	205	-	245	-	ns	
tec	Fast Page Mode Cycle Time	40	-	45	-	55	-	ns	
t _{PRMW}	Fast Page Mode Read-Modify-Write Cycle Time	95	-	100		120	_	ns	
t _{RAC}	Access Time from RAS	-	70	-	80	-	100	ns	9,14
t _{CAC}	Access Time from CAS	-	20	-	20		25	ns	9,14
taa	Access Time from Column Address	-	35	-	40	-	50	ns	9,15
t _{CPA}	Access Time from CAS Precharge	-	35	-	40	-	50	ns	9
tcız	CAS to output in Low-Z	0	_	0	_	0.	-	ns	9
toff	Output Buffer, Turn-off Delay	0	20	0	20	0	20	ns	10
t _T	Transition Time (Rise and Fall)	3	50	3	50	3	50	ns	8
t _{RP}	RAS Precharge Time	50	-	60	-	70		пs	
tras	RAS Pulse Width	70	10,000	80	10,000	100	10,000	ns	
trasp	RAS Pulse Width (Fast Page Mode)	70	100,000	80	100,000	100	100,000	ns	
t _{RSH}	RAS Hold Time	20	-	20	-	25	-	ПS	
trhcp	RAS Hold Time From CAS Precharge (Fast Page Mode)	35	_	40	-	50		ns	
t _{CSH}	CAS Hold Time	70		80		100		ns	
t _{CAS}	CAS Pulse Width	20	10,000	20	10,000	25	10,000	ns	L
t _{RCD}	RAS to CAS Delay Time	20	50	20	60	25	75	ns	14
trad	RAS to Column Address Delay Time	15	35	15	40	20	50	ns	15
t _{CRP}	CAS to RAS Precharge Time	5	-	5	1	5	•	ns	
t _{CP}	CAS Precharge Time	10	-	10	-	10		ns	
tasr	Row Address Set-Up Time	0	-	0	•	0	-	ns	
t _{RAH}	Row Address Hold Time	10	-	10	-	15	•	ns	
tasc	Column Address Set-Up Time	0	-	0	-	0	1	ns	
t _{CAH}	Column Address Hold Time	15	•	15	•	20	•	ns	
t _{AR}	Column Address Hold Time referenced to RAS	55	-	60	-	75	-	ns	
tRAL	Column Address to RAS Lead Time	35	-	40	-	50	-	ns	
t _{RCS}	Read Command Set-Up Time	0	-	0	-	0	-	ns	
t _{RCH}	Read Command Hold Time	0	_	0	_	0	-	ns	11
t _{RRH}	Read Command Hold Time referenced to RAS	0	-	0	-	0	-	ns	11
twcH	Write Command Hold Time	15	-	15	-	20	-	ns	

ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS (Continued)

SYMBOL	CHARACTERISTIC		4256AP/ /AZ-70		4256AP/ /AZ-80		14256AP/ /AZ-10	UNIT	NOTE
3		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
twcr	Write Command Hold Time referenced to RAS	55	-	60	-	75	-	រាទ	
twp	Write Command Pulse Width	15	-	15	-	20		ns	
trwL	Write Command to RAS Lead Time	20	-	20	-	25	-	ns	
t _{CWL}	Write Command to CAS Lead Time	20		20		25	-	ns	
tos	Data Set-Up Time	. 0	-	0		0		ns	12
t _{DH}	Data Hold Time	15	-	15	_	20	_	ns	12
tour	Data Hold Time referenced to RAS	55		60	-	75		ns	
tref	Refresh Period		8	_	8	-	8	ms	
twcs	Write Command Set-UP Time	0	•	0	-	0	-	ns	13
t _{CWD}	CAS to WRITE Delay Time	50	ł	50	-	60	-	ns	13
t _{RWD}	RAS to WRITE Delay Time	100	•	110	-	135	-	กร	13
tawd	Column Address to WRITE Delay Time	65	,	70	-	85		ns	13
tcpwD	CAS Precharge to WRITE Delay Time	65	-	70	_	85	_	ns	13
t _{CSR}	CAS Set-Up Time (CAS before RAS Cycle)	5	-	5	-	5	-	ns	
^t CHR	CAS Hold Time (CAS before KAS Cycle)	15	-	15	-	20	-	ns	
tapc	RAS to CAS Precharge Time	0	-	0	-	0	-	ns	
t _{CPT}	CAS Precharge Time (CAS before RAS Counter Test Cycle)	40	-	40	<u>-</u>	50	-	ns	
t _{ROH}	RAS Hold Time referenced to OE	10	-	10	-	20	-	ns	
toea	OE Access Time	-	20	_	20	-	25	ns	
toed	OE to Data Delay	20	-	20	-	25	-	ns	
t _{OEZ}	Output buffer turn off Delay Time from ŌE	0	20	0	20	0	25	ns	10
toen	OE Command Hold Time	20	-	20	-	25	-	ns	

CAPACITANCE ($V_{CC} = 5V \pm 10\%$, f = 1MHz, $T_a = 0 \sim 70$ °c)

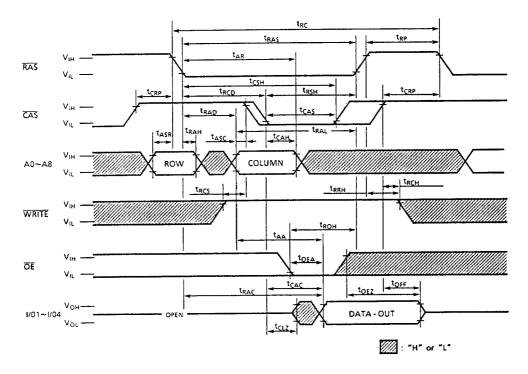
SYMBOL	CHARACTERISTIC	MIN.	MAX.	UNIT
C _{II}	Input Capacitance (A0~A8)	-	5	pF
C ₁₂	Input Capacitance (RAS, CAS, WRITE, OE)	-	7	pF
Co	Input/Output Capacitance (I/01~I/04)	_	7	pF

A-189

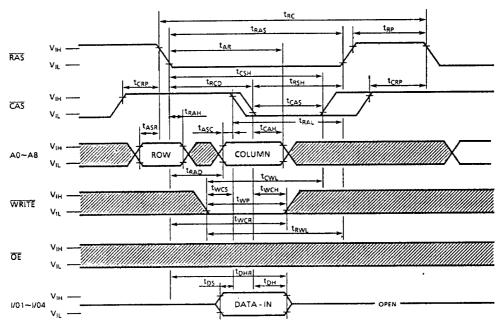
NOTES:

- Stresses greater than those listed under "Maximum Ratings" may cause permanent damage to the
 device.
- 2. All voltages are referenced to VSS.
- 3. ICC1, ICC3, ICC4 depend on cycle rate.
- 4. ICC1, ICC4, ICC6 depend on output loading. Specified values are obtained with the output open.
- 5. Column address can be changed once or less while $\overline{RAS} = V_{IL}$ and $\overline{CAS} = V_{IH}$.
- 6. An initial pause of 200µs is required after power-up followed by 8 RAS cycles before proper device operation is achieved. In case of using internal refresh counter, a minimum of 8 CAS before RAS initialization cycles instead of 8 RAS cycles are required.
- 7. AC measurements assume tr=5ns.
- 8. V_{IH} (min.) and V_{IL} (max.) are reference levels for measuring timing of input signals. Also, transition times are measured between V_{IH} and V_{IL} .
- 9. Measured with a load equivalent to 2 TTL loads and 100pF.
- 10. toff (max.) and toez (max.) define the time at which the output achieves the open circuit condition and are not referenced to output voltage levels.
- 11. Either tRCH or tRRH must be satisfied for a read cycle.
- 12. These parameters are referenced to CAS leading edge in early write cycles and to WRITE leading edge in Read-Modify-Write cycles.
- 13. twcs, t_{RWD}, t_{CWD}, t_{AWD} and t_{CPWD} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If twcs≥twcs (min.), the cycle is an early write cycle and the data out pin will remain open circuit (high impedance) through the entire cycle; If t_{RWD}≥t_{RWD} (min.), t_{CWD}≥t_{CWD} (min.), t_{AWD}≥t_{AWD} (min.) and t_{CPWD}≥t_{CPWD} (min.) (Fast Fage Mode), the cycle is a Read-Modify-Write cycle and the data out will contain data read from the selected cell: If neither of the above sets of conditions is satisfied, the condition of the data out (at access time) is indeterminate.
- 14. Operation within the t_{RCD} (max.) limit insures that t_{RAC} (max.) can be met. t_{RCD} (max.) is specified as a reference point only: If t_{RCD} is greater than the specified t_{RCD} (max.) limit, then access time is controlled by t_{CAC}.
- 15. Operation within the t_{RAD} (max.) limit insures that t_{RAC} (max.) can be met. t_{RAD} (max.) is specified as a reference point only: If t_{RAD} is greater than the specified t_{RAD} (max.) limit, then access time is controlled by t_{AA}.

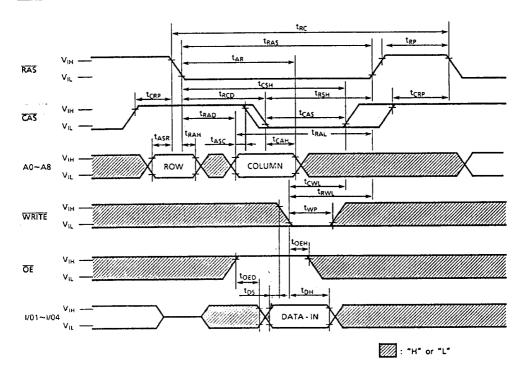
READ CYCLE



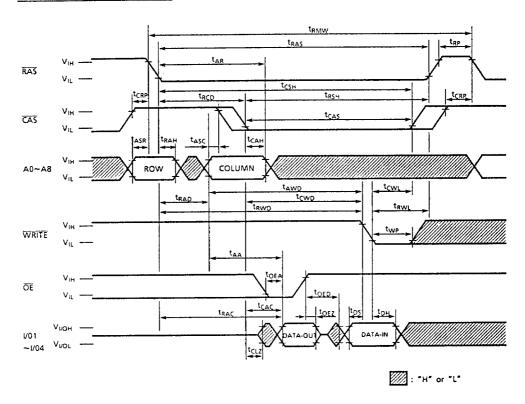
WRITE CYCLE (EARLY WRITE)



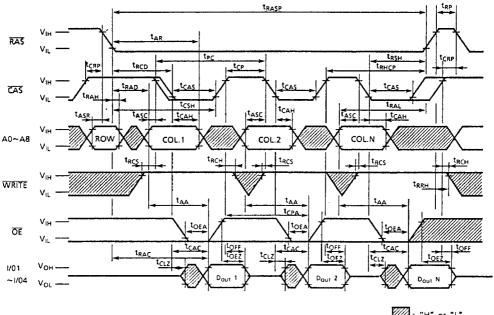
WRITE CYCLE (OE CONTROLLED WRITE)



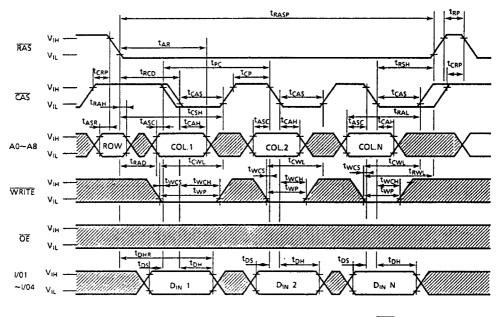
READ-MODIFY-WRITE CYCLE



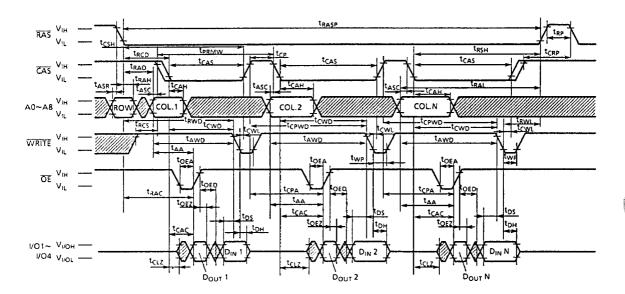
FAST PAGE MODE READ CYCLE



FAST PAGE MODE WRITE CYCLE

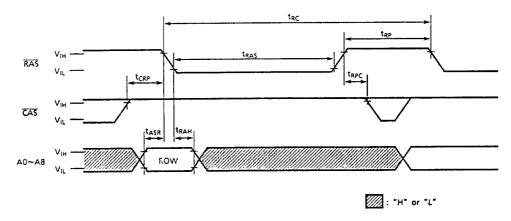


FAST PAGE MODE READ-MODIFY-WRITE CYCLE



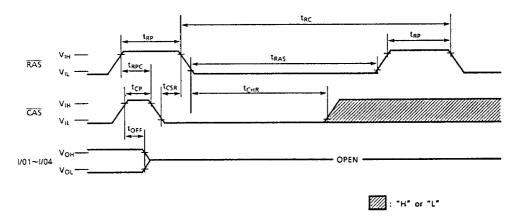


RAS ONLY REFRESH CYCLE



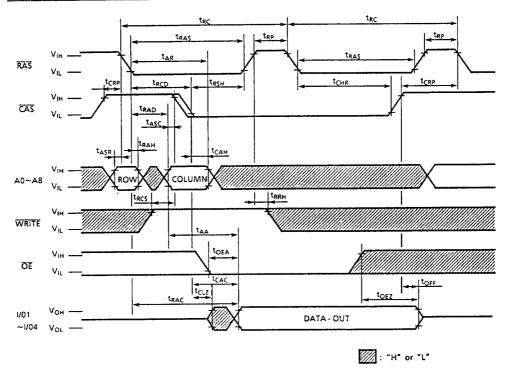
Note: WRITE, OE = "H" or "L"

CAS BEFORE RAS REFRESH CYCLE

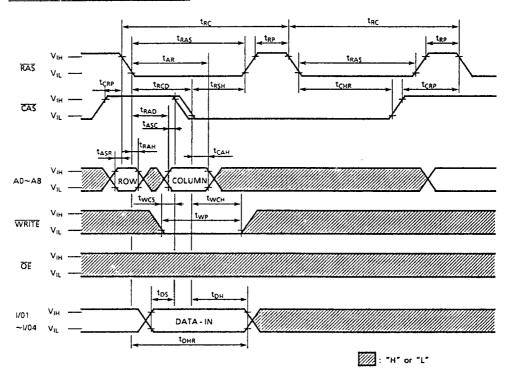


Note: WRITE, OE = A0~A8 = "H" or "L"

HIDDEN REFRESH CYCLE (READ)



HIDDEN REFRESH CYCLE (WRITE)



CAS BEFORE RAS REFRESH COUNTER TEST CYCLE

